# **Power Transistors**





TO - 220

#### Features:

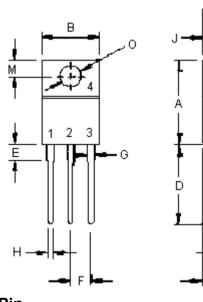
- Complementary Silicon Plastic Power Transistors ٠
- •
- Collector emitter sustaining voltage  $V_{CEO (sus)} = 60 V$  (minimum) Collector emitter saturation voltage  $V_{CE (sat)} = 1.5 V$  (maximum) at  $I_C = 6 A$ Current gain bandwidth product  $f_T = 3 MHz$  (minimum) at  $I_C = 500 mA$ •
  - •

#### **Applications:**

С

Designed for use in general purpose power amplifier and switching applications.

Dimensions : Millimetres



Dimensions	Minimum	m Maximum	
А	14.68	15.31	
В	9.78	10.42	
С	5.01	6.52	
D	13.06	14.62	
E	3.57	4.07	
F	2.42	3.66	
G	1.12	1.36	
Н	0.72	0.96	
I	4.22	4.98	
J	1.14	1.38	
К	2.2	2.97	
L	0.33	0.55	
М	2.48	2.98	
0	3.7	3.9	

#### Pin

1. Base

2. Collector

3. Emitter

4. Collector (Case)

### **Maximum Ratings**

Characteristics	Symbol	TIP41A TIP42A	Unit
Collector - emitter voltage	V <sub>CEO</sub>	60	V
Collector - base voltage	V <sub>CBO</sub>	60	V
Emitter - base voltage	V <sub>EBO</sub>	5	V
Collector current - Continuous - Peak	Ι <sub>C</sub>	6 10	A
Base current	Ι <sub>Β</sub>	2	A
Total power dissipation at T <sub>c</sub> = 25°C derate above 25°C	P <sub>D</sub>	65 0.52	W W/°C
Operating and storage Junction temperature range	T <sub>j,</sub> T <sub>stg</sub>	-65 to +150	°C

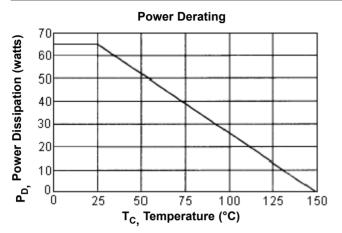
www.element14.com www.farnell.com www.newark.com





### **Thermal Characteristics**

Characteristic	Symbol	Maximum	Unit
Thermal resistance junction to case	$R_{ extsf{ heta}jc}$	1.92	°C/W



### Electrical Characteristics (Tc = 25°C Unless Otherwise noted)

Characteristics	Symbol	Minimum	Maximum	Units
Off Characteristics	1		<u> </u>	
Collector - emitter sustaining voltage (1) $(I_C = 30 \text{ mA}, I_B = 0)$	V <sub>CEO (SUS)</sub>	60	-	V
Collector cut off current $(V_{CE} = 100 \text{ V}, I_B = 0)$	I <sub>CEO</sub>	-	0.7	mA
Collector cut off current $(V_{CE} = 60 \text{ V}, V_{BE} = 0)$	I <sub>CES</sub>	-	0.4	mA
Emitter cut off current ( $V_{EB} = 5 \text{ V}, I_{C} = 0$ )	I <sub>EBO</sub>	-	1	mA
On Characteristics (1)	1		L	
DC current gain ( $I_C = 0.3 \text{ A}; V_{CE} = 4 \text{ V}$ ) ( $I_C = 0.3 \text{ A}; V_{CE} = 4 \text{ V}$ )	h <sub>FE</sub>	30 15	75	-
Collector - emitter saturation voltage $(I_C = 6 \text{ A}; I_B = 600 \text{ mA})$	V <sub>CE (sat)</sub>	-	1.5	V
Base-emitter on voltage $(I_C = 6 A; V_{CE} = 4 V)$	V <sub>BE (on)</sub>	-	2	V
Dynamic characteristics				
Current gain-bandwidth Product (2) ( $I_C$ = 500 mA; $V_{CE}$ = 10 V, $f_{TEST}$ = 1 MHz)	f <sub>T</sub>	3	-	MHz
Small signal current gain (I <sub>C</sub> = 500 mA; V <sub>CE</sub> = 10 V, f = 1 kHz)	h <sub>fe</sub>	20	-	-

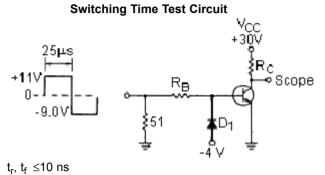
(1) Pulse test: Pulse width  $\leq 300~\mu s,~duty~cycle \leq 2\%$ 

(2)  $f_T = |h_{fe}| \bullet f_{TEST}$ 



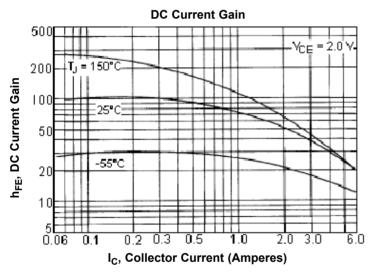
# **Power Transistors**

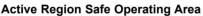


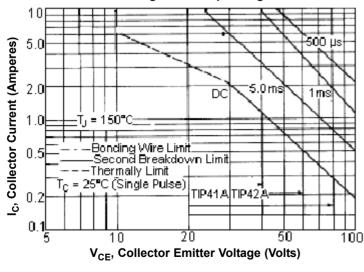


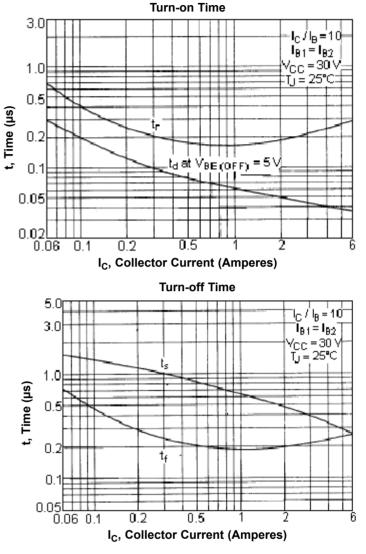
Duty cycle = 1%

 $R_{B}$  and  $R_{C}$  varied to obtain desired current levels  $D_{1}$  must be fast recovery type eg: M8D5000 Used Above  $I_{B}$  to 100 mA MSD6100 Used Below  $I_{B}$  to 100 mA









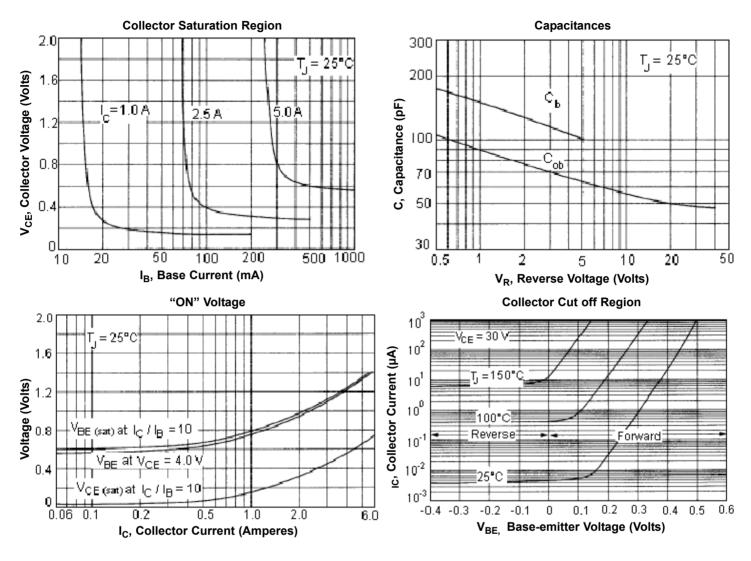
There are two limitation on the power ability of a transistor: average junction temperature and second breakdown safe operating area curves indicate  $I_C\text{-}V_{CE}$  limits of the transistor that must be observed for reliable operation i.e., the transistor must not be subjected to greater dissipation than curves indicate. The data of curve is base on  $T_{J\ (PK)}$  = 150°C;  $T_C$  is variable depending on power level. Second breakdown pulse limits are valid for duty cycles to 10% provided  $T_{J\ (PK)} \leq 150^\circ\text{C}$ , at high case temperatures, thermal limitation will reduce the power that can be handled to less than the limitations imposed by second breakdown.



www.element14.com www.farnell.com www.newark.com

# **Power Transistors**





#### **Part Number Table**

Description	Part Number
Transistor, NPN, TO-220	TIP41A
Transistor, PNP, TO-220	TIP42A

Important Notice : This data sheet and its contents (the "Information") belong to the members of the Premier Famell group of companies (the "Group") or are licensed to it. No licence is granted for the use of it other than for information purposes in connection with the products to which it relates. No licence of any intellectual property rights is granted. The Information is subject to change without notice and replaces all data sheets previously supplied. The Information supplied is believed to be accurate but the Group assumes no responsibility for its accuracy or completeness, any error in or omission from it or for any use made of it. Users of this data sheet should check for themselves the Information and the suitability for loss or damage resulting from any reliance on the Information or use of it (including liability resulting from negligence or where the Group was aware of the possibility of such loss or damage raising) is excluded. This will not operate to limit or restrict the Group's liability for death or personal injury resulting from its negligence. Multicomp is the registered trademark of the Group. © Premier Farnell plc 2011.



www.element14.com www.farnell.com www.newark.com